
Yuki Tanaka ¹

Hideki Matsuoka ¹, Masaki Nakano^{1,2}, Yoshihiro Iwasa^{1,2}

¹ Department of Applied Physics, Univ. of Tokyo, Tokyo, Japan

² Center for Emergent Matter Science (CEMS), RIKEN, Wako, Japan

tanaka@mp.t.u-tokyo.ac.jp

Superconducting properties of highly-strained 3R-TaSe₂ epitaxial thin films

Transition metal dichalcogenides (TMDs) draw much attention because of their intriguing properties emerging at two-dimensional (2D) limit. Nowadays, some groups have succeeded in exfoliation of metallic TMDs such as NbSe₂ and TaS₂ down to a monolayer limit, unveiling new aspects of 2D physical properties. One remarkable example is unconventional superconductivity achieved by combination of large spin-orbit coupling and broken inversion symmetry, where spin-momentum-locked Cooper pairs play an important role in their superconducting states [1,2]. Another unique feature is the relationship between superconductivity and charge-density wave (CDW), which has been discussed both in NbSe₂ and TaS₂ exfoliated flakes. In this work, we focus on TaSe₂, which has been also known to have similar electronic structure and exhibit both superconductivity and CDW in its bulk form. There is one paper reporting electronic structure of monolayer TaSe₂ [3], but electrical transport properties of TaSe₂ ultrathin films have not been investigated so far. In this presentation, we report on fabrication of high-quality 3R-TaSe₂ thin films by molecular beam epitaxy, and show their transport properties with reduced dimensions.

References

- [1] X. Xi *et al.*, *Nat. Phys.* 12 (2016) 139-143
- [2] S. C. de la Barrera *et al.*, *Nat. Commun.* 9 (2018) 1427
- [3] H. Ryu *et al.*, *Nano Lett.* 18 (2018) 689-694

Figures

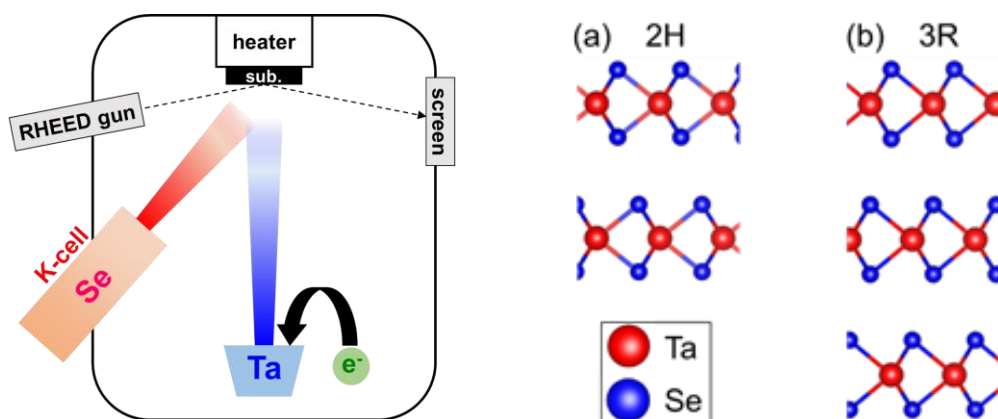


Figure 1: (Left) Schematic image of MBE (Right) (a)2H and (b)3R poly-types of TaSe₂